

ABSTRACT

Provided in the present invention is a chemical mechanical polishing solution for improving the TEOS polishing rate. The chemical mechanical polishing solution comprises a nitrogen-containing heterocyclic conjugated compound, and cerium oxide particles having negative charges ($\text{Zeta} \leq 30 \text{ mV}$). By using the described technical solution, the chemical mechanical polishing solution can significantly improve the TEOS polishing rate, and in addition, can achieve the effects of simplifying the cleaning process after polishing, improving the product yield and productivity, and reducing the production costs.

(No suitable figure)